

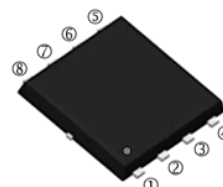
RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

DESCRIPTION

The SPR118N06S-C is the highest performance N-ch MOSFETs with extreme high cell density, which provide excellent $R_{DS(ON)}$ and gate charge for most of the synchronous rectification applications.

The SPR118N06S-C meet the RoHS and Green Product requirement with full function reliability approved.

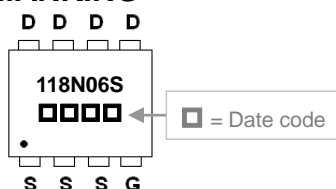
PR-8PP



FEATURES

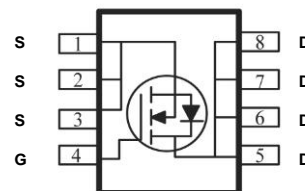
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

MARKING



PACKAGE INFORMATION

Package	MPQ	Leader Size
PR-8PP	3K	13 inch



ORDER INFORMATION

Part Number	Type
SPR118N06S-C	Lead (Pb)-free and Halogen-free

ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ¹ @ $V_{GS}=10\text{V}$	I_D	$T_C=25^\circ\text{C}$	118
		$T_C=100^\circ\text{C}$	75
Pulsed Drain Current ²	I_{DM}	240	A
Total Power Dissipation ³	P_D	83.3	W
Operating Junction & Storage Temperature Range	T_J, T_{STG}	-55~150	$^\circ\text{C}$
Thermal Data			
Thermal Resistance Junction-Ambient ¹	$R_{\theta JA}$	55	$^\circ\text{C} / \text{W}$
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	1.5	

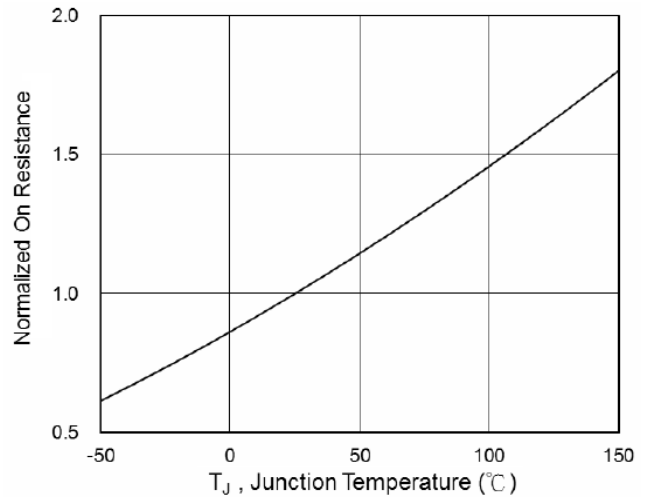
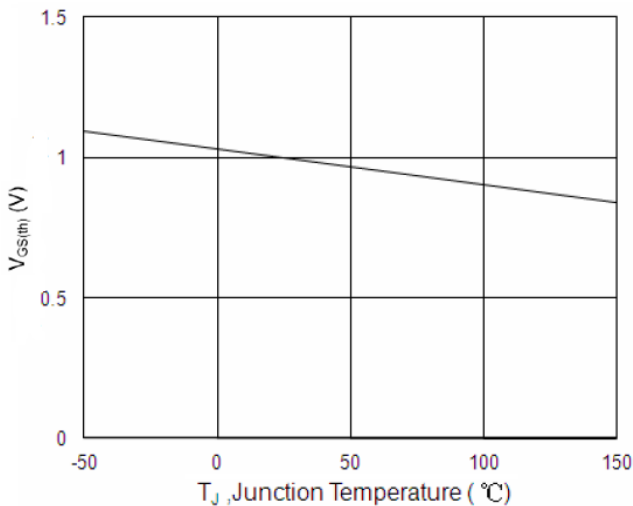
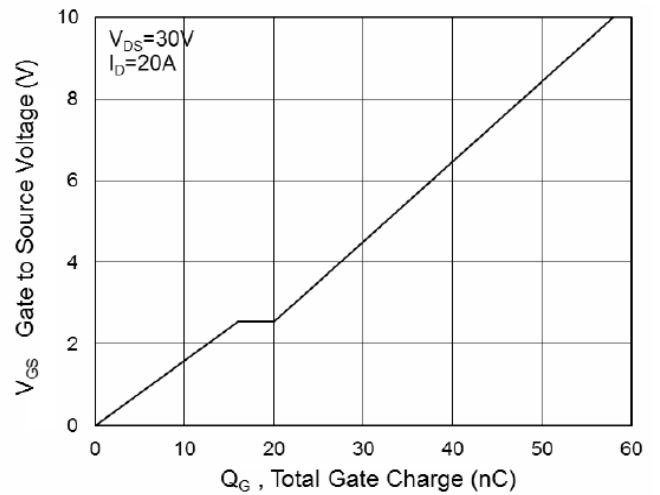
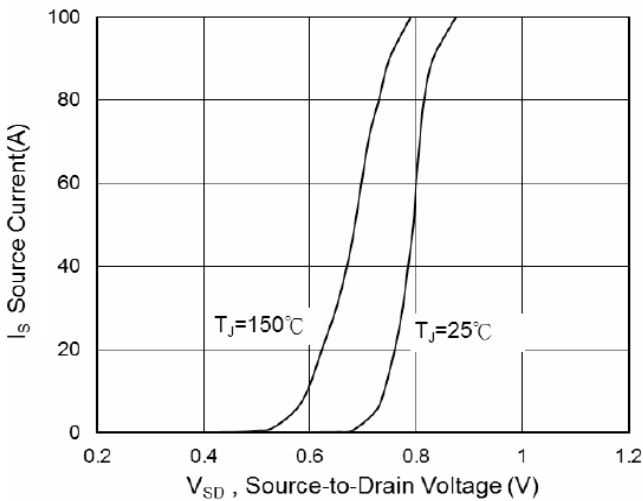
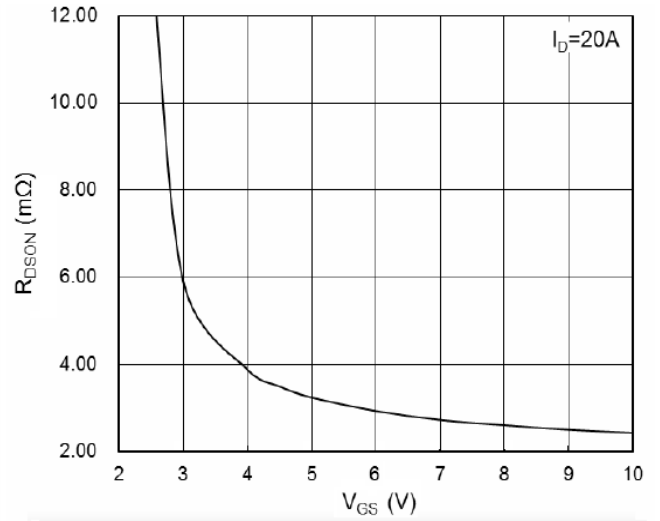
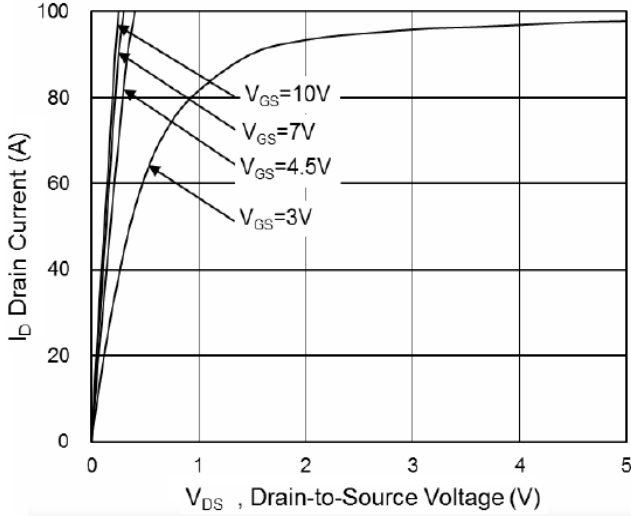
ELECTRICAL CHARACTERISTICS ($T_J=25^\circ C$ unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage	BV_{DSS}	60	-	-	V	$V_{GS}=0V, I_D=250\mu A$
Gate-Threshold Voltage	$V_{GS(th)}$	1	-	2.5	V	$V_{DS}=V_{GS}, I_D=250\mu A$
Forward Transfer conductance	g_{fs}	-	65	-	S	$V_{DS}=5V, I_D=20A$
Gate-Source Leakage Current	I_{GSS}	-	-	± 100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Drain-Source Leakage Current	I_{DSS}	-	-	1	μA	$V_{DS}=48V, V_{GS}=0V, T_J=25^\circ C$
		-	-	5		$V_{DS}=48V, V_{GS}=0V, T_J=55^\circ C$
Static Drain-Source On-Resistance ²	$R_{DS(ON)}$	-	3	3.6	m Ω	$V_{GS}=10V, I_D=20A$
		-	4.4	5.7		$V_{GS}=4.5V, I_D=15A$
Gate Resistance	R_g	-	0.7	-	Ω	$f=1MHz$
Total Gate Charge	Q_g	-	58	-	nC	$I_D=20A$ $V_{DS}=30V$ $V_{GS}=10V$
Gate-Source Charge	Q_{gs}	-	16	-		
Gate-Drain Change	Q_{gd}	-	4	-		
Turn-on Delay Time	$T_{d(on)}$	-	18	-	nS	$V_{DD}=30V$ $I_D=20A$ $V_{GS}=10V$ $R_G=3\Omega$
Rise Time	T_r	-	8	-		
Turn-off Delay Time	$T_{d(off)}$	-	50	-		
Fall Time	T_f	-	10.5	-		
Input Capacitance	C_{iss}	-	3458	-	pF	$V_{GS}=0V$ $V_{DS}=30V$ $f=1MHz$
Output Capacitance	C_{oss}	-	1042	-		
Reverse Transfer Capacitance	C_{rss}	-	22	-		
Source-Drain Diode						
Diode Forward Voltage ²	V_{SD}	-	-	1.2	V	$I_S=1A, V_{GS}=0V, T_J=25^\circ C$
Continuous Source Current ¹	I_S	-	-	118	A	$V_G=V_D=0V, \text{Force Current}$
Reverse Recovery Time	t_{rr}	-	24	-	nS	$I_F=20A, dI/dt=100A/\mu s,$ $T_J=25^\circ C$
Reverse Recovery Charge	Q_{rr}	-	85	-	nC	

Notes:

1. The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
2. The data tested by pulsed pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. The power dissipation is limited by 150°C junction temperature.

CHARACTERISTIC CURVES



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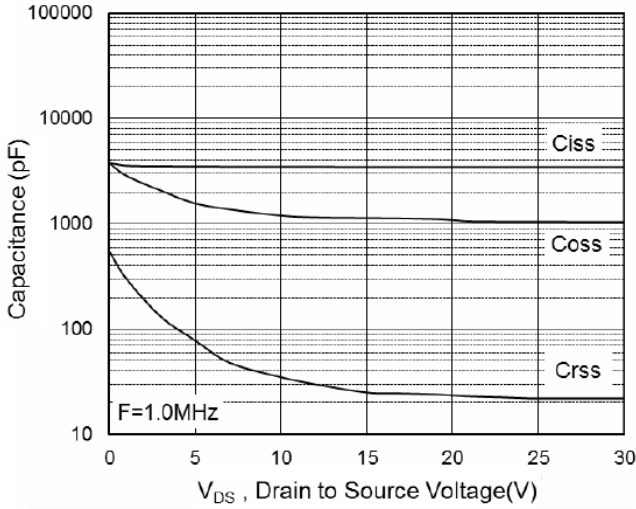


Fig.7 Capacitance

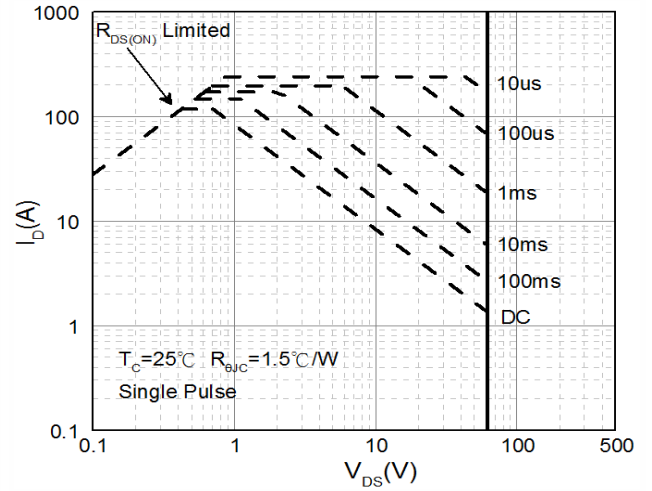


Fig.8 Safe Operating Area

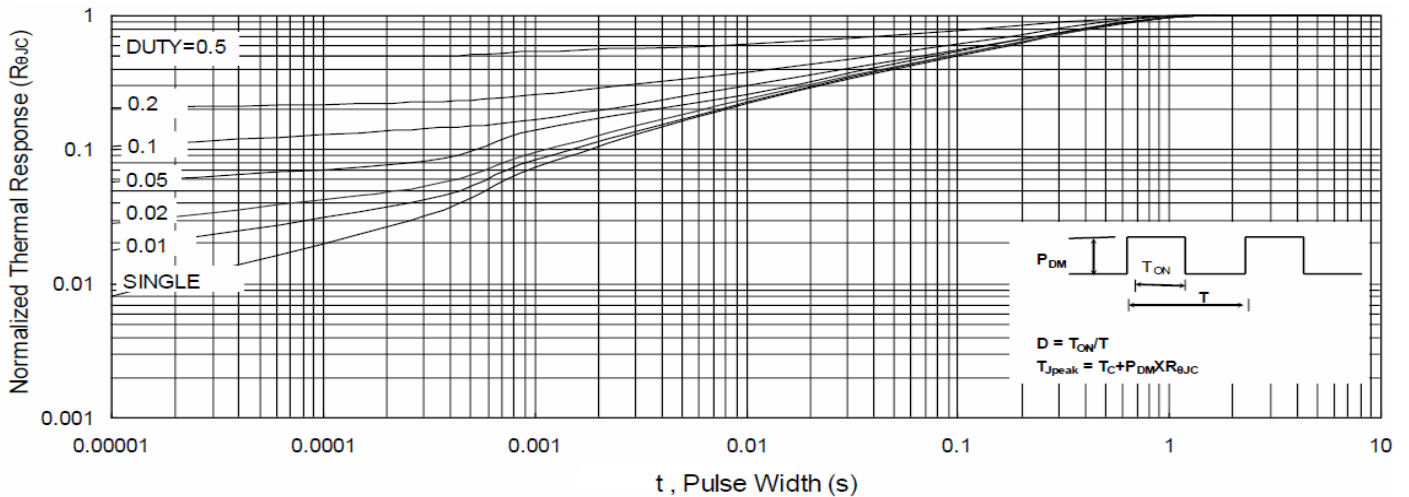


Fig.9 Normalized Maximum Transient Thermal Impedance

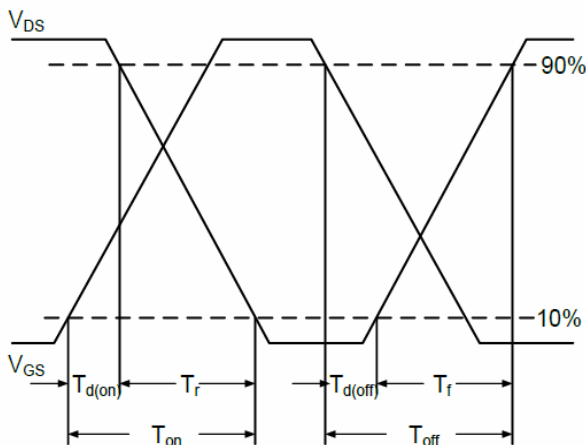


Fig.10 Switching Time Waveform

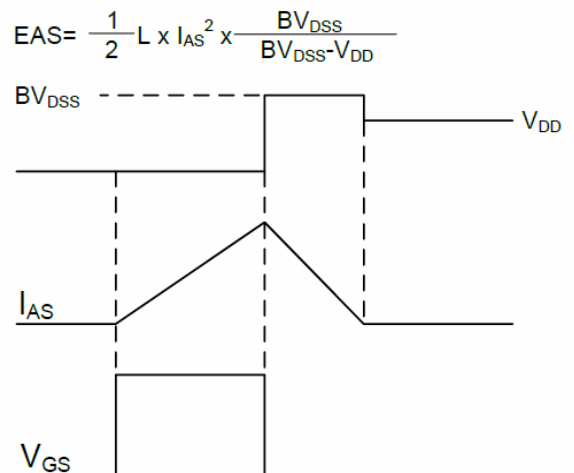
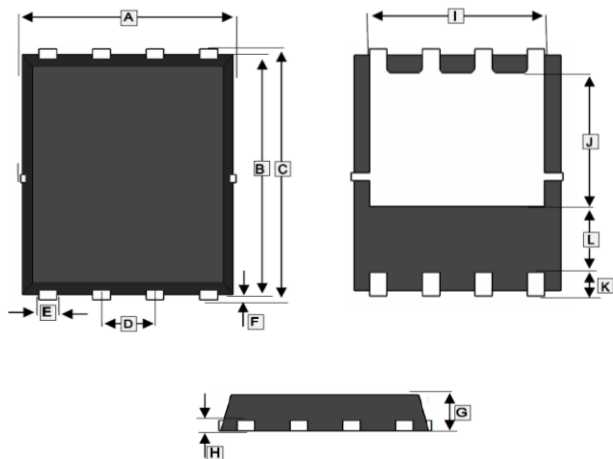


Fig.11 Unclamped Inductive Switching Waveform

PACKAGE OUTLINE DIMENSIONS

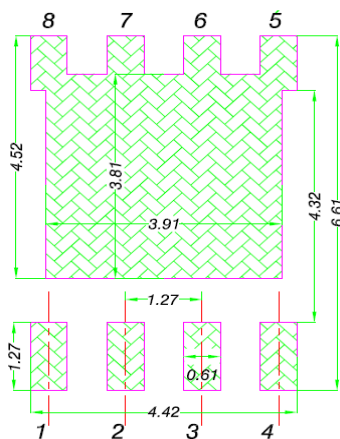
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REF.	Millimeter	
	Min.	Max.
A	4.90	5.10
B	5.70	5.90
C	5.90	6.20
D	1.27 BSC.	
E	0.33	0.51
F	0.06	0.20
G	0.80	1.10
H	0.254 REF.	
I	4.00 REF.	
J	3.40 REF.	
K	0.60 REF.	
L	1.40 REF.	

MOUNTING PAD LAYOUT

PR-8PP



*Dimensions in millimeters